



#14/B  
8/20/01  
Harran

PATENT  
Attorney Docket No.: 002818/PDD/PSI/JW

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Suketu A. Parikh

Serial No.: 09/244,788

Filed: 2/5/99

For: Dual Damascene Misalignment  
 Tolerant Techniques For Vias And  
 Sacrificial Etch Segments

- ) Group: TC 2000 MAIL ROOM
- ) Art Unit: 2813
- ) Examiner: Pham T.
- )
- ) Clean Amended Claims In Response to
- ) Notice of Non-Compliance dated 7/23/01
- )
- ) PATENT COUNSEL
- ) APPLIED MATERIALS, INC.
- ) Legal Affairs Department
- ) P.O. Box 450 A
- ) Santa Clara, CA 95052

Assistant Commissioner for Patents  
 Washington, D.C. 20231

Sir:

## CLEAN AMENDED CLAIMS

This response regarding clean amended claims is in response to a Notice of Non-Compliant Amendment (37 CFR 1.121) dated 7/23/01. The clean amended claims provided herein, concern the marked up amended claims in applicant's Amendment and Response that was filed with the Patent and Trademark Office on 6/29/01. The Examiner is respectfully requested to replace original "as filed" claims 1, 11, 13, 14, 19, 21, 29 and 31 with the following clean amended claims 1, 11, 13, 14, 19, 21, 29 and 31.

- 
1. (once amended) A method of forming a structure on a substrate, the method comprising:
- a) depositing a first dielectric layer on the substrate;
  - b) depositing a second dielectric layer on the first dielectric layer, wherein the first and second dielectric layers comprise materials having dissimilar etching characteristics;
  - c) depositing a first mask layer on the second dielectric layer, wherein the first mask layer includes a first via pattern having a width T;
  - d) anisotropically etching the first via pattern through the second dielectric layer;
  - e) removing the first mask;